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Octal D-type Flip Flops with 3-state Outputs



ADE-205-071B(Z)

Rev.2 September 1995

Description

The HD74LVC534 has eight edge trigger D type flip flops with three state outputs in a 20 pin package. Data at the D inputs meeting set up reguirements, are transferred to the Q outputs on positive going transitions of the clock input. When the latch enable goes low, data at the D inputs will be retained at the outputs until latch enable returns high again. When a high logic level is applied to the output control input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements. Low voltage and high speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

- $V_{cc} = 2.0 \text{ V to } 5.5 \text{ V}$
- All inputs V_{IH} (Max.) = 5.5 V (@V_{CC} = 0 V to 5.5 V)
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current ± 24 mA (@V_{cc} = 3.0 V to 5.5 V)

Function Table

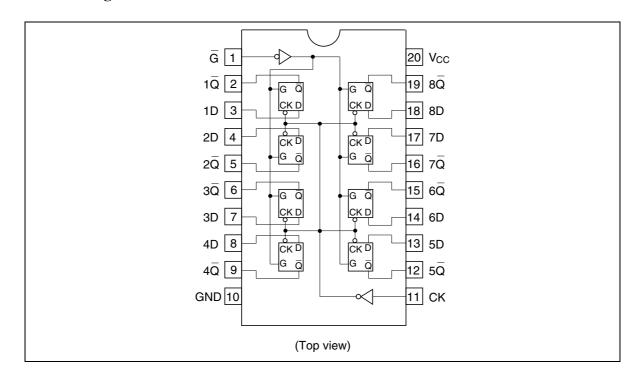
Inputs

G	СК	D	Output Q
Н	X	Χ	Z
L	↑	L	Н
L	↑	Н	L
L	L	X	Q_0

H: High level
L: Low level
X: Immaterial
Z: High impedance
↑: Low to high transition

 $Q_{_0}$: Level of \overline{Q} before the indicated steady input conditions were established.

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	-0.5 to 6.0	V	
Input diode current	I _{IK}	– 50	mA	V ₁ = -0.5 V
Input voltage	V,	-0.5 to 6.0	V	
Output diode current	I _{ok}	– 50	mA	V ₀ = -0.5 V
		50	mA	$V_0 = V_{cc} + 0.5 \text{ V}$
Output voltage	V _o	–0.5 to $V_{\rm cc}$ +0.5	V	
Output current	Io	±50	mA	
V _{cc} , GND current / pin	$I_{\rm cc}$ or $I_{\rm GND}$	100	mA	
Storage temperature	Tstg	-65 to +150	°C	

Note: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	1.5 to 5.5	V	Data retention
		2.0 to 5.5	V	At operation
Input / output voltage	V,	0 to 5.5	V	G, CK, D
	V_{\circ}	0 to V _{cc}	V	Q
Operating temperature	Та	-40 to 85	°C	
Output current	I _{OH}	–12	mA	V _{cc} = 2.7 V
		-24 ^{*2}	mA	$V_{cc} = 3.0 \text{ V to } 5.5 \text{ V}$
	I _{oL}	12	mA	V _{cc} = 2.7 V
		24*2	mA	$V_{cc} = 3.0 \text{ V to } 5.5 \text{ V}$
Input rise / fall time *1	t _r , t _r	10	ns/V	

Notes: 1. This item guarantees maximum limit when one input switches.

Waveform : Refer to test circuit of switching characteristics.

2. duty cycle $\leq 50\%$

Electrical Characteristics

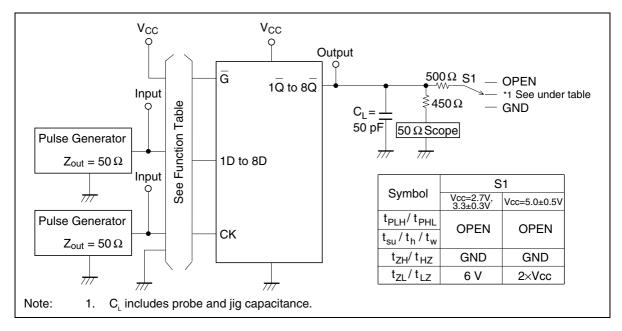
 $Ta = -40 \text{ to } 85^{\circ}C$

Item	Symbol	V _{cc} (V)	Min	Max	_ Unit	Test Conditions
Input voltage	V _{IH}	2.7 to 3.6	2.0	_	V	
		4.5 to 5.5	V _{cc} ×0.7	_	V	-
	V _{IL}	2.7 to 3.6	_	0.8	V	
		4.5 to 5.5	_	V _{cc} ×0.3	V	-
Output voltage	V _{OH}	2.7 to 5.5	V _{cc} -0.2	_	V	$I_{OH} = -100 \mu A$
		2.7	2.2	_	V	I _{OH} = -12 mA
		3.0	2.4	_	V	-
		3.0	2.0	_	V	I _{OH} = -24 mA
		4.5	3.8	_	V	-
	V _{oL}	2.7 to 5.5	_	0.2	V	I _{OL} = 100 μA
		2.7	_	0.4	V	I _{OL} = 12 mA
		3.0	_	0.55	V	I _{oL} = 24 mA
		4.5	_	0.55	V	-
Input current	I _{IN}	0 to 5.5	_	±5.0	μΑ	V _{IN} = 5.5 V or GND
Off state output current	l _{oz}	5.5	_	±10	μА	$V_{IN} = V_{CC}$, GND $V_{OUT} = V_{CC}$ or GND
Quiescent supply current	I _{cc}	5.5	_	20	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{cc}	3.0 to 3.6	_	500	μΑ	$V_{\rm IN}$ = one input at($V_{\rm cc}$ -0.6)V, other inputs at $V_{\rm cc}$ or GND

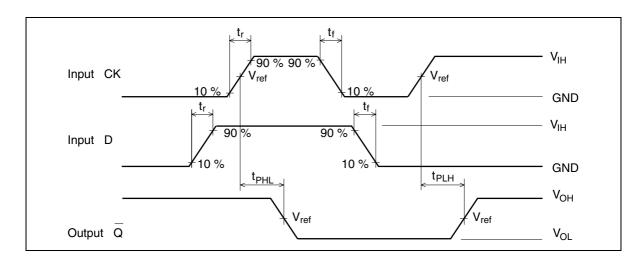
Switching Characteristics

		Ta = −40 to 85°C						
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	From (Input)	To (Output)
Maximum clock frequency	f _{max}	2.7	80.0	_	_	MHz		
		3.3±0.3	100.0	150.0	_	MHz	_	
		5.0±0.5	125.0	_	_	MHz	_	
Propagation delay time	t _{PLH}	2.7	_	7.0	9.5	ns	CK	Q
	$t_{\scriptscriptstylePHL}$	3.3±0.3	1.5	5.5	8.5	ns	_	
		5.0±0.5	_	4.0	7.0	ns	_	
Output enable time	t _{zн}	2.7	_	7.0	9.5	ns	G	Q
	$t_{_{ZL}}$	3.3±0.3	1.5	5.5	8.5	ns	_	
		5.0±0.5	_	4.0	7.0	ns	_	
Output disable time	t _{HZ}	2.7	_	5.0	8.5	ns	G	Q
	$\mathbf{t}_{\scriptscriptstyle{LZ}}$	3.3±0.3	1.5	4.5	7.5	ns	_	
		5.0±0.5	_	3.5	6.5	ns	_	
Setup time	t _{su}	2.7	2.0	_	_	ns		
		3.3±0.3	2.0	_		ns	_	
		5.0±0.5	2.0	_		ns	_	
Hold time	t _h	2.7	1.5	_	_	ns		
		3.3±0.3	1.5	_	_	ns	_	
		5.0±0.5	1.5	_	_	ns	_	
Pulse width	t _w	2.7	4.0	_	_	ns		
		3.3±0.3	4.0	_	_	ns	_	
		5.0±0.5	3.0	_	_	ns	_	
Input capacitance	C _{IN}	2.7	_	3.0	_	pF		
Output capacitance	C _o	2.7	_	15.0	_	pF		

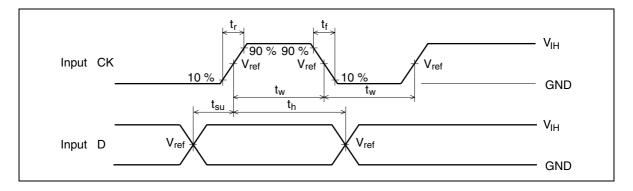
Test Circuit



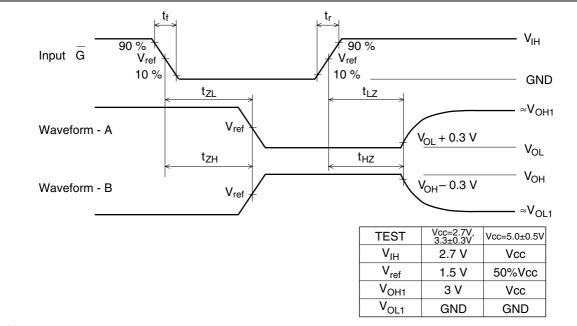
Waveforms - 1



Waveforms - 2



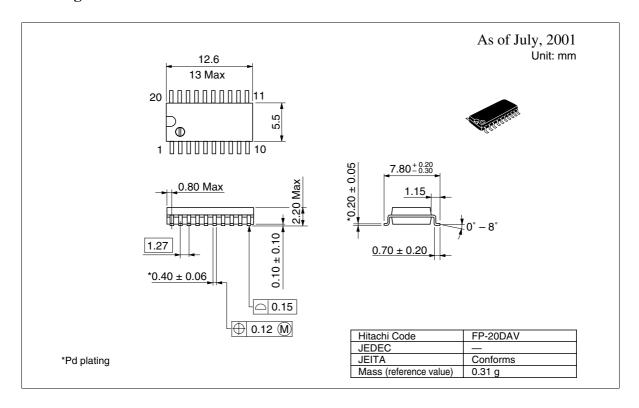
Waveforms - 3

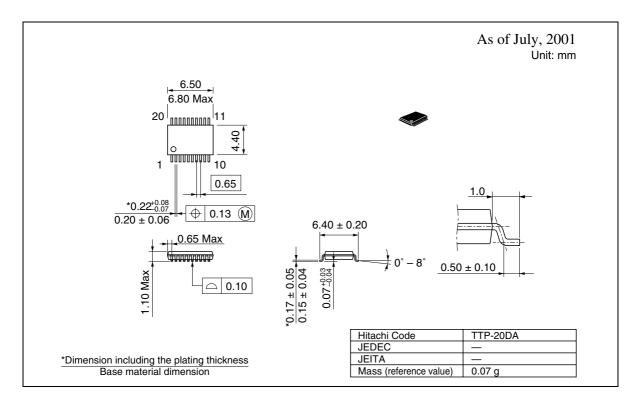


Notes:

- 1. $t_r = 2.5 \text{ ns}, t_r = 2.5 \text{ ns}$
- 2. Input waveform : PRR = 10 MHz, duty cycle 50%
- 3. Waveform A shows input conditions such that the output is "L" level when enable by the output control.
- 4. Waveform B shows input conditions such that the output is "H" level when enable by the output control.

Package Dimensions





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